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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application / Conf. No.	Unknown /
				Filing Date	October 24, 2003
				First Named Inventor	Kevin T. Look
				Art Unit	Unknown
				Examiner Name	Unknown
Sheet	1	of	2	Attorney Docket Number	X-719-ID-ID US

U.S. PATENT DOCUMENTS					
Examiner Initials *	Cite No. *	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code (if known)			
MG		US- 5,627,400	05-06-92	Koga	
MG		US- 5,656,528	08-12-97	Wahlstrom	
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FOREIGN PATENT DOCUMENTS						
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		Country Code *	Number - Kind Code * (if known)			
MG		JP	40623289 A	08-01-94	Kou	
MG		JP	360009160 A	01-18-85	Fukumoto et al.	
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MG		JP	363079377 A	04-09-88	Kita	
MG		JP	406163906 A	06-10-94	Natsume	

Examiner Signature	<i>Yana Guenero</i>	Date Considered	9-29-04
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Sheet	2	of	2

OTHER -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MG		"Boron Diffusion And Penetration In Ultrathin Oxide With Poly-Si Gate"; Cao et al.; IEEE Electron Device Letters; Vol. 19; No. 8; August 1998; pp. 291-293	
MG		"Flat-band Voltage Shifts In P-MOS Devices Caused By Carrier Activation In P+-Polycrystalline Silicon and Boron Penetration"; Aoyama et al.; 1997 IEEE; pp. 26.1.1 - 26.1.4	
MG		"A PROM Element Based On Salicide Agglomeration Of Poly Fuses In A CMOS Logic Process"; Alavi et al.; 1997 IEEE; pp. 34.3.1 - 34.3.4	
MG		"Effects Of Thermal Processes After Silicidation On The Performance Of TiSi ₂ /Polysilicon Gate Device"; Jang et al.; IEEE Transactions On Electron Devices; Vol. 46; No. 12; December 1999; pp. 2353-2356	
MG		"Comparison Of Transformation To Low-Resistivity Phase And Agglomeration Of TiSi ₂ and CoSi ₂ "; Lasky et al.; IEEE Transaction On Electron Devices; Vol. 38; No. 2; February 1991; pp. 262-269	
MG		"CoSi ₂ Integrated Fuses On Poly Silicon For Low Voltage 0.18 um CMOS Application"; Kalnitsky et al.; 1999 IEEE; 4 pages	

Examiner Signature	<i>Maria Guerrero</i>	Date Considered	9-29-04
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